

Ordering number : ENN7264

P-Channel Silicon MOSFET

**CPH3319**

## Ultrahigh-Speed Switching Applications

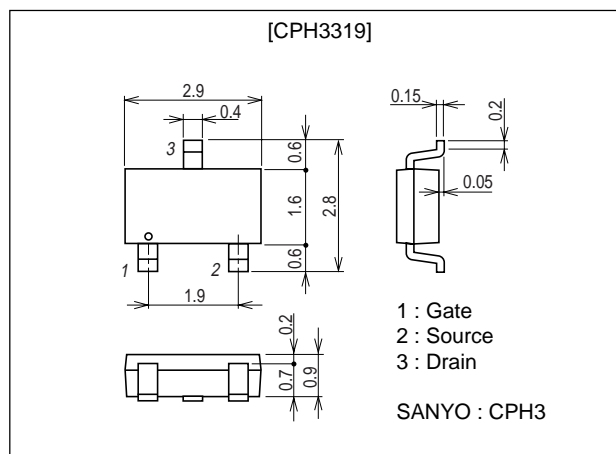
### Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 1.8V drive.

### Package Dimensions

unit : mm

2152A



### Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-12	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±8	V
Drain Current (DC)	I <sub>D</sub>		-1.5	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-6	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm²×0.8mm)	0.9	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0	-12			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-12V, V <sub>GS</sub> =0			-10	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±6.4V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-6V, I <sub>D</sub> =-1mA	-0.3		-1.0	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-6V, I <sub>D</sub> =-0.8A	1.3	1.8		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-0.8A, V <sub>GS</sub> =-4.5V		220	290	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-0.4A, V <sub>GS</sub> =-2.5V		320	450	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =-0.1A, V <sub>GS</sub> =-1.8V		430	650	mΩ

Marking : JU

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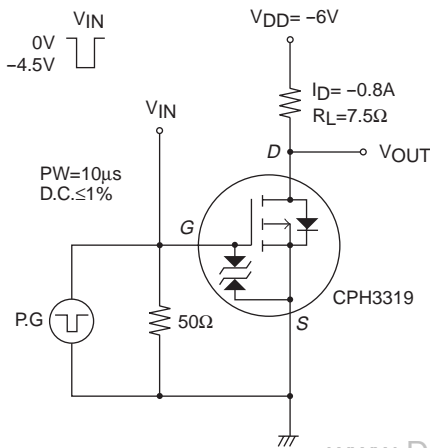
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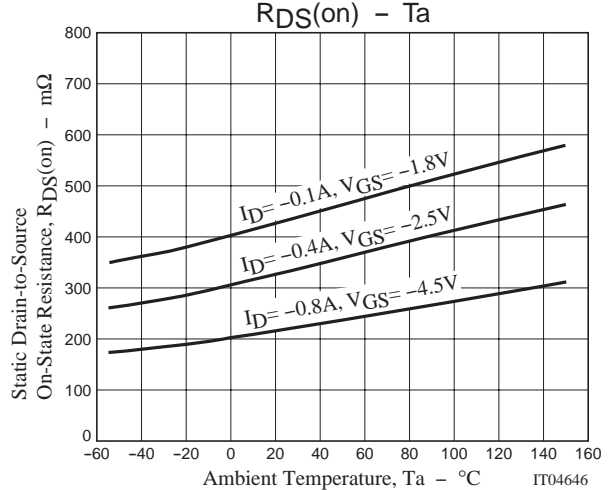
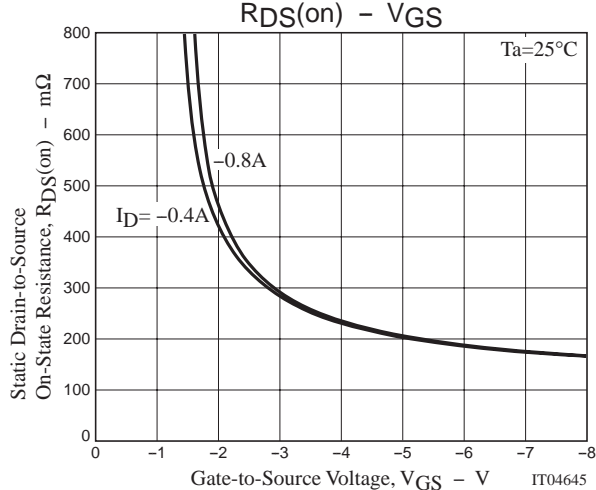
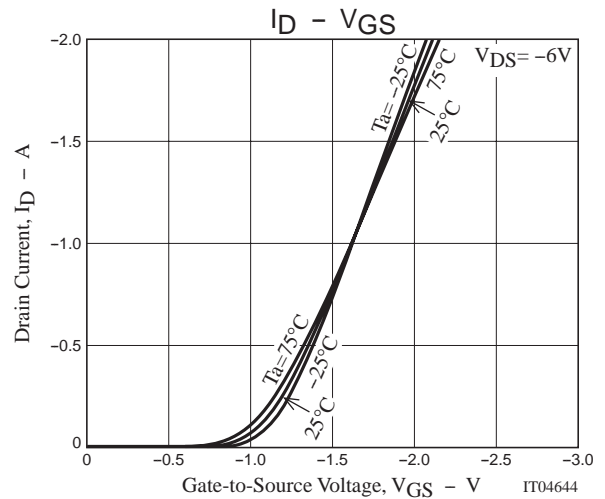
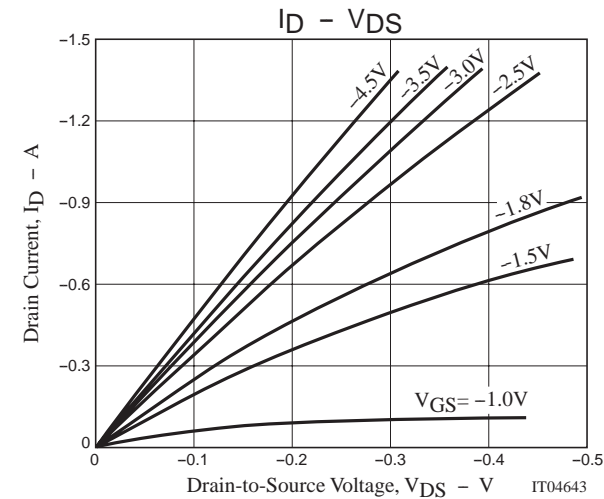
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	VDS=-6V, f=1MHz		160		pF
Output Capacitance	Coss	VDS=-6V, f=1MHz		45		pF
Reverse Transfer Capacitance	Crss	VDS=-6V, f=1MHz		35		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		11		ns
Rise Time	tr	See specified Test Circuit.		45		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		29		ns
Fall Time	tf	See specified Test Circuit.		30		ns
Total Gate Charge	Qg	VDS=-6V, VGS=-4.5V, ID=-1.5A		2.6		nC
Gate-to-Source Charge	Qgs	VDS=-6V, VGS=-4.5V, ID=-1.5A		0.25		nC
Gate-to-Drain "Miller" Charge	Qgd	VDS=-6V, VGS=-4.5V, ID=-1.5A		0.65		nC
Diode Forward Voltage	VSD	IS=-1.5A, VGS=0	-0.92		-1.5	V

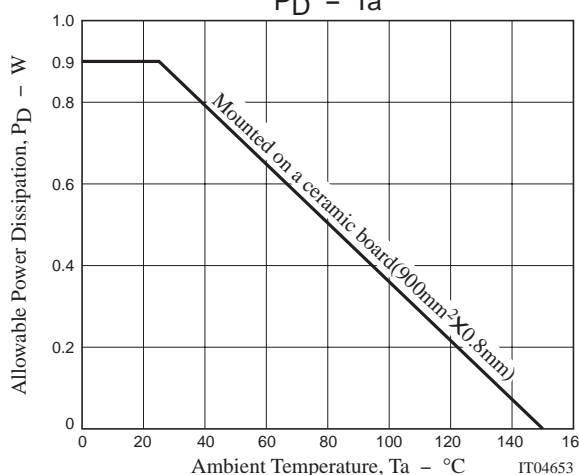
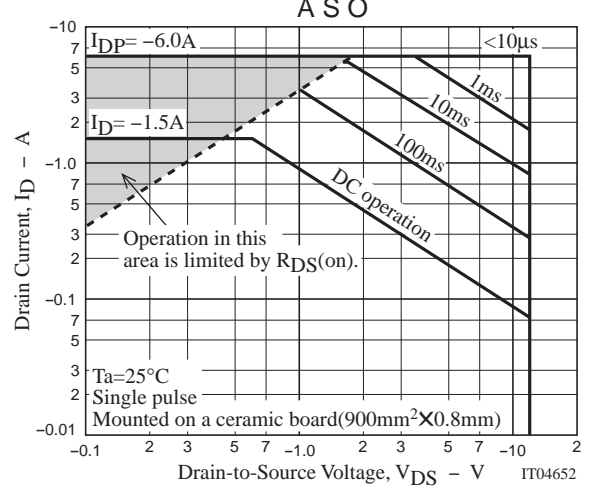
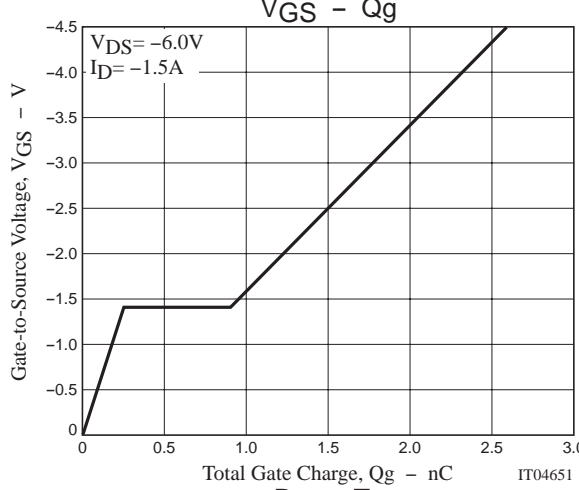
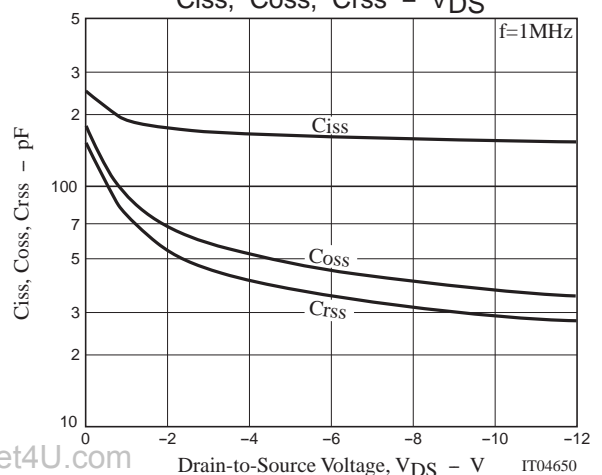
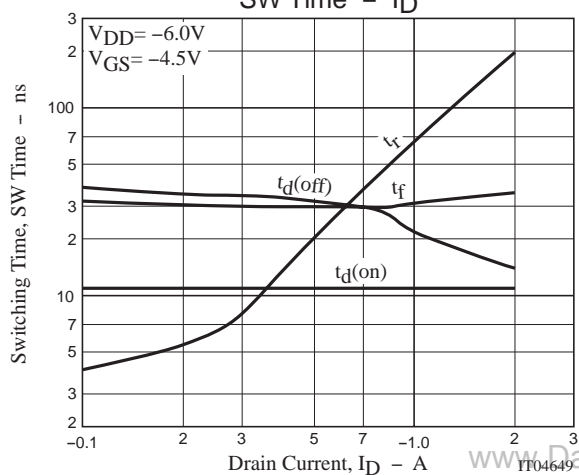
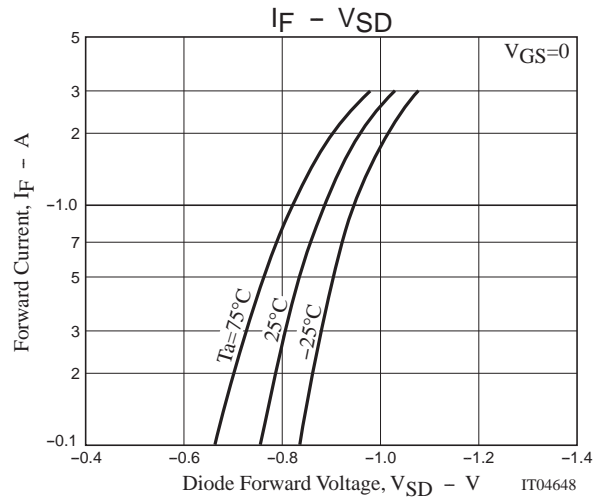
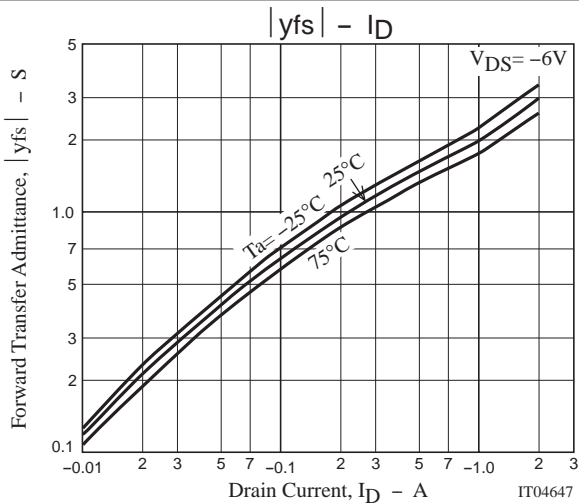
## Switching Time Test Circuit



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